

GAAS SOLAR BATTERY ELEMENT

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要約 JP57204180

PURPOSE: To miniaturize for high reliability owing to the decrease of the number of wirings and unnecessary of diode occupation area, etc. by monolithic integration of diodes for inverse voltage prevention into each element on manufacturing a solar battery element. **CONSTITUTION:** An N type first GaAs region 2, P type second GaAs region 3 and P type first AlGaAs region 4 are successively formed on one wider side of a substrate 1 and N type third GaAs region 5, P type forth GaAs region 6 and P type second AlGaAs region 7 on the other narrower side. The regions 2-4 constitute a solar battery and regions 5-7 an inverse voltage preventing diode. Thus, array integration unnecessitates diodes to simplify wiring for the enhancement of reliability with miniaturization.

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